

## **KH231**

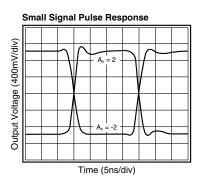
# Fast Settling, Wideband Buffer/Amplifier ( $A_V = \pm 1$ to $\pm 5$ )

#### **Features**

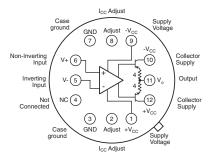
- 165MHz closed-loop -3dB bandwidth
- 15ns settling to 0.05%
- 1mV input offset voltage, 10µV/°C drift
- 100mA output current
- Excellent AC and DC linearity
- Direct replacement for CLC231

### **Applications**

- Driving flash A/D converters
- Precision line driving (a gain of 2 cancels matched-line losses)
- DAC current-to-voltage conversion
- Low-power, high-speed applications (50mW @ ±5V)



#### **Bottom View**



Pins 2 and 8 are used to adjust the supply current or to adjust the offset voltage (see text). These pins are normally left unconnected.

#### **Typical Performance**

_ *.							
	Gain Setting						
Parameter	1	2	5	-1	-2	-5	Units
-3dB bandwidth	180	165	130	165	150	115	MHz
rise time (2V)	1.8	2.0	2.5	2.0	2.2	2.9	ns
slew rate	2.5	3.0	3.0	3.0	3.0	3.0	V/ns
settling time (to 0.1%)	12	12	12	12	12	15	ns

### **General Description**

The KH231 Buffer/Amplifier is a wideband operational amplifier designed specifically for high-speed, low-gain applications. The KH231 is based on a current feedback op amp topology-a unique design that both eliminates the gain-bandwidth tradeoff and permits unprecedented high-speed performance. (See table below.)

The KH231 Buffer/Amplifier is the ideal design alternative to low precision open-loop buffers and oscillation-prone conventional op amps. The KH231 offers precise gains from  $\pm 1.000$  to  $\pm -5.000$  and linearity that is a true 0.1%-even for demanding  $50\Omega$  loads. Open-loop buffers, on the other hand, offer a nominal gain of 0.95  $\pm 0.03$  and a linearity of only 3% for typical loads. A buffer's settling time may look impressive but it is usually specified at unrealistically large load resistances or when the effects of thermal tail are not included; the KH231 Buffer/Amplifier settles to 0.05% in 15ns-while driving a  $100\Omega$  load.

Offsets and drifts, usually a low priority in conventional high-speed op amp designs, were not ignored in the KH231; the input offset voltage is typically 1mV and input offset voltage drift is only  $10\mu V/^{\circ}C$ . The KH231 is stable and oscillation-free across the entire gain range and since it's internally compensated, the user is saved the trouble of designing external compensation networks and having to "tweak" them in production. The absence of a gain-bandwidth tradeoff in the KH231 allows performance to be predicted easily; the table below shows how the bandwidth is affected very little by changing the gain setting.

The KH231 is constructed using thin film resistor/bipolar transistor technology, and is available in the following versions:

The KH231 is constructed using thin film resistor/bipolar transistor technology, and available in these versions:

KH231AI	-25°C to +85°C	12-pin TO-8 can
KH231AK	-55°C to +125°C	12-pin TO-8 can, features burn-in & hermetic testing
KH231AM	-55°C to +125°C	12-pin TO-8 can, environmentally screened and electrically tested to MIL-STD-883
KH231HXC	-55°C to +125°C	SMD#: 5962-8959401HXC
KH231HXA	-55°C to +125°C	SMD#: 5962-8959401HXA

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KH231 Electrical Characteristics ( $T_A = +25^{\circ}C$ ,  $A_V = +2V$ ,  $V_{CC} = \pm 15V$ ,  $R_L = 100\Omega$ ,  $R_f = 250\Omega$ ; unless specified)

PARAMETERS	CONDITIONS	TYP MIN & MAX RATINGS		UNITS	SYM		
Ambient Temperature	KH231AI	+25°C	-25°C	+25°C	+85°C		
Ambient Temperature	KH231AK/AM/HXC/HXA	+25°C	-55°C	+25°C	+125°C		
FREQUENCY DOMAIN RESPONSE  † -3dB bandwidth (note 2)  Warge-signal bandwidth gain flatness (note 2)	V <sub>o</sub> ≤2V <sub>pp</sub> V <sub>o</sub> ≤10V <sub>pp</sub> V <sub>o</sub> ≤2V <sub>pp</sub>	165 95	>145 >80	>145 >80	>120 >60	MHz MHz	SSBW FPBW
t peaking t peaking t rolloff group delay linear phase deviation reverse isolation	V <sub>0</sub> ≤2V <sub>pp</sub> 0.1 to 50MHz >50MHz at 100MHz to 100MHz to 100MHz	0.1 0.1 0.4 3.5 ± 0.5 0.5	<0.6 <1.5 <0.6 - <2.0	<0.3 <0.3 <0.6 - <2.0	<0.6 <0.8 <1.0 - <2.0	dB dB dB ns	GFPL GFPH GFR GD LPD
non-inverting inverting		53 36	>43 >26	>43 >26	>43 >26	dB dB	RINI RIIN
rise and fall time  settling time to 0.05% to 0.1% overshoot slew rate (overdriven input) overload recovery	2V step 10V step 5V step 2.5V step 5V step <1% error	2.0 5.0 15 12 5 3.0	<2.4 <7.0 - <22 <15 >2.5	<2.3 <6.5 - <17 <10 >2.5	<2.7 <6.5 - <22 <15 >1.8	ns ns ns ns % V/ns	TRS TRL TS TSP OS SR
<50ns pulse, 200% overdrive		120	_	_	_	ns	OR
<ul> <li>NOISE AND DISTORTION RESPONS</li> <li>2nd harmonic distortion</li> <li>3rd harmonic distortion</li> <li>equivalent input noise</li> <li>noise floor</li> <li>integrated noise</li> </ul>	E 0dBm, 20MHz 0dBm, 20MHz >5MHz 5MHz to 200MHz	-55 -59 -153 70	<-47 <-47 <-150 <100	<-47 <-47 <-150 <100	<-47 <-47 <-150 <100	dBc dBc dBm(1Hz) μVrms	HD2 HD3 SNF INV
* input offset voltage     average temperature coefficient  * input bias current     average temperature coefficient  * input bias current     average temperature coefficient  * input bias current     average temperature coefficient  * power supply rejection ratio common mode rejection ratio  * supply current	non-inverting inverting no load	1 10 5.0 50 10 125 50 46 18	<4.0 <25 <29 <125 <31 <200 >45 >40 <22	<2.0 <25 <21 <125 <15 <200 >45 >40 <22	<4.5 <25 <31 <125 <35 <200 >45 >40 <22	mV μV/°C μA nA/°C μA nA/°C dB dB mA	VIO DVIO IBN DIBN IBI DIBI PSRR CMRR ICC
MISCELLANEOUS PERFORMANCE non-inverting input resistance non-inverting input capacitance output impedance output voltage range	DC @ 100MHz no load	400 1.3 5, 37 ±12	>100 <2.5 - >±11	>200 <2.5 - >±11	>400 <2.5 - >±11	kΩ pF Ω, nH V	RIN CIN RO VO

Min/max ratings are based on product characterization and simulation. Individual parameters are tested as noted. Outgoing quality levels are determined from tested parameters.

#### **Absolute Maximum Ratings**

 $V_{CC}$ ±20V ±100mA common mode input voltage, Vo (see V<sub>cm</sub> and V<sub>o</sub> limits plot on page 3) differential input voltage ±3V thermal resistance (see thermal model) junction temperature +175°C AI: -25°C to +85°C operating temperature AK/AM: -55°C to +125°C storage temperature -65°C to +150°C +300°C lead temperature (soldering 10s)

note 1: \* AI/AK/AM/HXC/HXA 100% tested at +25°C

t AK/AM/HXC/HXA 100% tested at +25°C and sample tested at -55°C and +125°C

† Al sample tested at +25°C

**note 2:** The output amplitude used in testing is 0.63V<sub>pp</sub>. Performance is guaranteed for conditions listed.

## **Recommended Operating Conditions**

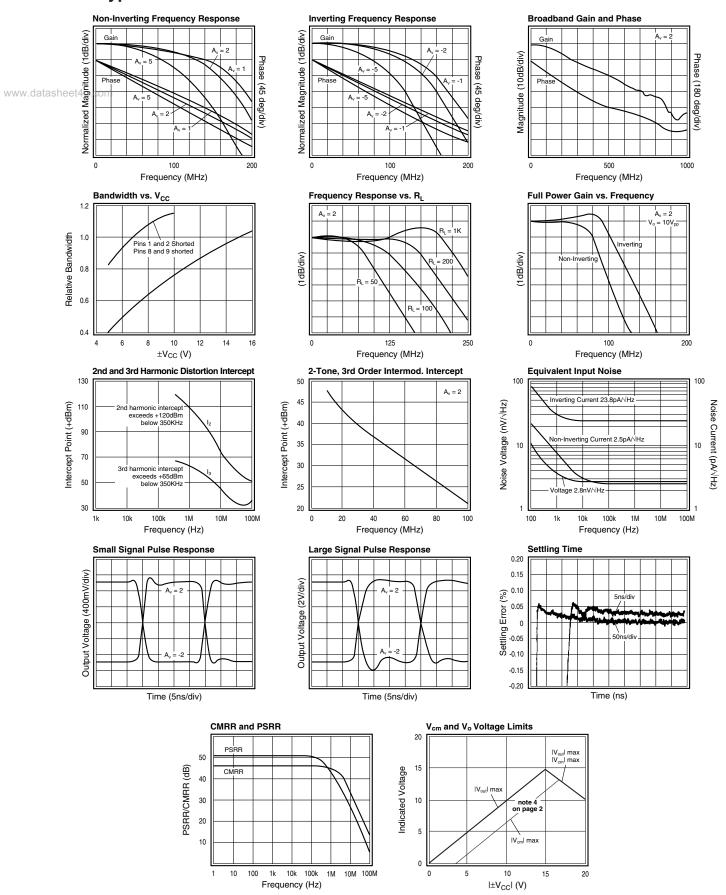
 $\begin{array}{ccc} V_{CC} & \pm 5V \text{ to } \pm 15V \\ I_o & \pm 75\text{mA} \\ \text{common mode input voltage} & \pm (|V_{CC}| - 5)V \\ \text{gain range} & \pm 1 \text{ to } \pm 5 \end{array}$ 

**note 3:** In the noninverting configuration, care should be taken when choosing  $R_i$ , the input impedance setting resistor; bias currents of typically  $5\mu A$  but as high as  $24\mu A$  can create an input signal large enough to cause overload. It is therefore recommended that  $R_i < (V_{CC}/A_v)/24\mu A$ .

note 4: These ratings protect against damage to the input stage caused by saturation of either the input or output stages at lower supply voltages, and against exceeding transistor collector-emitter breakdown ratings at high supply voltages. Vout(max) is calculated by assuming no output saturation. Saturation is allowed to occur up to this calculated level of Vout. Vcm is defined as the voltage at the non-inverting input, pin 6.

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## KH231 Typical Performance Characteristics ( $T_A = +25^{\circ}\text{C}$ , $A_v = +2$ , $V_{CC} = \pm 15\text{V}$ , $R_L = 100\Omega$ , $R_f = 250\Omega$ ; unless specified)



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#### Operation

The KH231 Buffer/Amplifier is based on the current feedback op amp topology, a design that uses current feedback instead of the usual voltage feedback.

The use of the KH231 is basically the same as that of the conventional op amp (see Figures 1 and 2). Since the widevice is designed specifically for low gain applications, the best performance is obtained when the circuit is used at gains between ±1 and ±5. Additionally, performance is optimum when a 250Ω feedback resistor is used.

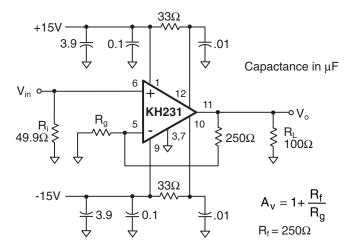


Figure 1: Recommended non-inverting gain circuit

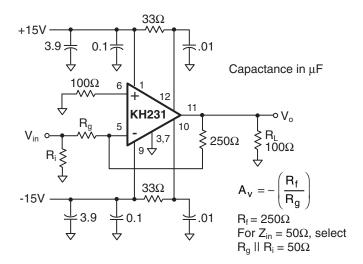


Figure 2: Recommended inverting gain circuit

#### **Lavout Considerations**

To assure optimum performance the user should follow good layout practices which minimize the unwanted coupling of signals between nodes. During initial breadboarding of the circuit use direct point to point wiring, keeping the lead lengths to less than 0.25". The use of solid, unbroken ground plane is helpful. Avoid wire-wrap

type pc boards and methods. Sockets with small, short pin receptacles may be used with minimal performance degradation although their use is not recommended.

During pc board layout keep all traces short and direct The resistive body of R<sub>a</sub> should be as close as possible to pin 5 to minimize capacitance at that point. For the same reason, remove ground plane from the vicinity of pins 5 and 6. In other areas, use as much ground plane as possible on one side of the board. It is especially important to provide a ground return path for current from the load resistor to the power supply bypass capacitors. Ceramic capacitors of 0.01 to 0.1µf (with short leads) should be less than 0.15 inches from pins 1 and 9. Larger tantalum capacitors should be placed within one inch of these pins. V<sub>CC</sub> connections to pins 10 and 12 can be made directly from pins 9 and 1, but better supply rejection and settling time are obtained if they are separately bypassed as in figures 1 and 2. To prevent signal distortion caused by reflections from impedance mismatches, use terminated microstrip or coaxial cable when the signal must traverse more than a few inches.

Since the pc board forms such an important part of the circuit, much time can be saved if prototype boards of any high frequency sections are built and tested early in the design phase. Evaluation boards designed for either inverting or non-inverting gains are available.

#### **Distortion and Noise**

The graphs of intercept point,  $I_2$  and  $I_3$ , versus frequency on the preceding page make it easy to predict the distortion at any frequency given the output voltage of the KH231. First, convert the output voltage  $(V_o)$  to  $V_{rms} = (V_{pp}/2\sqrt{2})$  and then to  $P = [(10log_{10}(20V_{rms}^2))]$  to get the power output in dBm. At the frequency of interest, its 2nd harmonic will be  $S_2 = (I_2\text{-P})\text{dB}$  below the level of P. Its third harmonic will be  $S_3 = 2(I_3\text{-P})\text{dB}$  below P, as will the two-tone third order intermodulation products. These approximations are useful for P < -1dB compression levels.

Approximate noise figure can be determined for the KH231 using the equivalent input noise graph on the preceding page. The following equation can be used to determine noise figure (F) in dB.

$$F = 10\log \left[ 1 + \frac{V_n^2 + \frac{i_n^2 R_f^2}{A_v^2}}{4kTR_s \Delta f} \right]$$

Where  $V_n$  is the rms noise voltage and  $i_n$  is the rms noise current. Beyond the breakpoint of the curves (i.e., where they are flat), broadband noise figure equals spot noise figure, so  $\Delta f$  should equal one (1) and  $V_n$  and  $i_n$  should be read directly off the graph. Below the breakpoint, the noise must be integrated and  $\Delta f$  set to the appropriate bandwidth f

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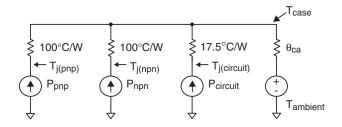
#### Offset Voltage Adjustment

If trimming of the input offset voltage ( $V_{os} = V_{ni} - V_{in}$ ) is desired, a resistor value of  $10k\Omega$  to  $1M\Omega$  placed between pins 8 and 9 will cause  $V_{os}$  to become more negative by 8mV to 0.2mV respectively. Similarly, a resistor placed between pins 1 and 2 will cause  $V_{os}$ , to become more positive.

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#### **Thermal Considerations**

At high ambient temperatures or large internal power dissipations, heat sinking is required to maintain acceptable junction temperatures. Use the thermal model on the previous page to determine junction temperatures. Many styles of heat sinks are available for TO-8 packages; the Thermalloy 2240 and 2268 are good examples. Some heat sinks are the radial fin type which cover the pc board and may interfere with external components. An excellent solution to this problem is to use surface mounted resistors and capacitors. They have a very low profile and actually improve high frequency performance. For use of these heat sinks with conventional components, a 0.1" high spacer can be inserted under the TO-8 package to allow sufficient clearance.



$$P_{(circuit)} = (I_{CC})((+V_{CC}) - (V_{CC}))$$
 where  $I_{CC} = 16 mA$  at  $\pm 15 V$ 

$$\mathsf{P}_{(\mathsf{xxx})} = \left[ (\pm \mathsf{V}_{\mathsf{CC}}) - \mathsf{V}_{\mathsf{out}} - (\mathsf{I}_{\mathsf{col}}) \; (\mathsf{R}_{\mathsf{col}} + 4) \right] (\mathsf{I}_{\mathsf{col}}) \; (\%\mathsf{Duty})$$

For positive  $V_o$  and  $V_{CC}$ , this is the power in the npn device. For negative  $V_o$  and  $V_{CC}$ , this is the power in the pnp device.

 $I_{col} = V_o/R_L$  or 4mA, whichever is greater. (Include feedback R in  $R_L$ .)

 $\rm R_{col}$  is a resistor (33 $\Omega$  recommended) between the xxx collector and  $\pm \rm V_{CC}.$ 

The limiting factor for output current and voltage is junction temperature. Of secondary importance is  $I_{(out)}$ , which should not exceed 150mA.

$$T_{j(pnp)} = P_{(pnp)} (100 + \theta_{ca}) + (P_{(cir)} + P_{(npn)})(\theta_{ca}) + T_a$$
, similar for  $T_{j(npn)}$ .

$$T_{j(cir)} = P_{(cir)}(48 + \theta_{ca}) + (P_{(pnp)} + P_{(npn)})(\theta_{ca}) + T_a.$$

 $\theta_{\text{ca}}$  = 65°C/W for the KH231 without heat sink in still air. 30°C/W for the KH231 with a Wakefield 215 heat sink in still air.

10°C/W for the KH231 with a Wakefield 215 heat sink at 300 ft/min air.

30°C/W for the KH231 with a Thermalloy 2240A heat sink in still air.

5°C/W for the KH231 with a Thermalloy 2240A heat sink at 500 ft/min air.

For example, with the KH231 operating at  $\pm 15V$  while driving a  $100\Omega$  load at  $15V_{pp}$  output (50% duty cycle pulse waveform, DC = 0),  $P_{(npn)} = P_{(pnp)} = 190$ mW ( $R_{col} = 33$ ) and  $P_{(cir)} = 0.4$ 8W. Then with the Wakefield 215 heat sink and air flow of 300 ft/min the output transistors'  $T_j$  is 28°C above ambient and worst case  $T_j$  in the rest of the circuit is 32°C above ambient. In still air, however, the rise in  $T_j$  is 45°C and 49°C, respectively. With no heat sink, the rise in  $T_j$  is 75°C and 79°C, respectively! Under most conditions, **HEAT SINKING IS REQUIRED**.

Other methods of heat sinking may be used, but for best results, make contact with the base of the KH231 package, use a large thermal capacity heat sink and use forced air convection.

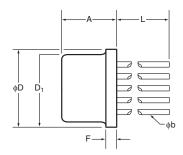
### Low V<sub>CC</sub> Operation: Supply Current Adjustment

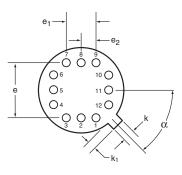
The KH231 is designed to operate on supplies as low as  $\pm 5$ V. In order to improve full bandwidth at reduced supply voltages, the supply current (I<sub>CC</sub>) must be increased. The plot of Bandwidth vs. V<sub>CC</sub>, shows the effect of shorting pins 1 and 2 and pins 8 and 9; this will increase both bandwidth and supply current. Care should be taken to not exceed the maximum junction temperatures; for this reason this technique should not be used with supplies exceeding  $\pm 10$ V. For intermediate values of V<sub>CC</sub>, external resistors between pins 1 and 2 and pins 8 and 9 can be used.

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## **KH231 Package Dimensions**

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TO-8						
SYMBOL	INC	HES	MILIMETERS			
	Minimun	Maximum	Minimum	Maximum		
А	0.142	0.181	3.61	4.60		
φb	0.016	0.019	0.41	0.48		
φD	0.595	0.605	15.11	15.37		
φD <sub>1</sub>	0.543	0.555	13.79	14.10		
е	0.400	BSC	10.16 BSC			
e <sub>1</sub>	0.200	) BSC	5.08 BSC			
e <sub>2</sub>	0.100	) BSC	2.54 BSC			
F	0.016	0.030	0.41	0.76		
k	0.026	0.036	0.66	0.91		
k <sub>1</sub>	0.026	0.036	0.66	0.91		
L	0.310	0.340	7.87	8.64		
α	45°	BSC	45° BSC			

#### NOTES:

Seal: cap weld Lead finish: gold per MIL-M-38510 Package composition: Package: metal

Lid: Type A per MIL-M-38510

#### Life Support Policy

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